

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

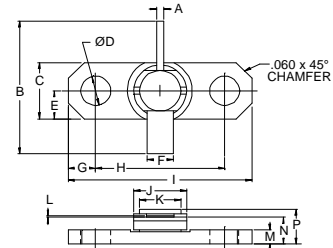
The ASI OSC-1.3SH is Designed for

FEATURES:

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- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	700 mA
V_{CC}	30 V
P_{DISS}	17.6 W @ T _C ≤ 50 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +200 °C
θ_{JC}	8.5 °C/W

PACKAGE STYLE .250 2L FLG


DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.028 / 0.71	.032 / 0.81
B	.740 / 18.80	
C	.245 / 6.22	.255 / 6.48
D	.128 / 3.25	.132 / 3.35
E		.125 / 3.18
F	.110 / 2.79	.117 / 2.97
G		.117 / 2.97
H	.560 / 14.22	.570 / 14.48
I	.790 / 20.07	.810 / 20.57
J	.225 / 5.72	.235 / 5.97
K	.165 / 4.19	.185 / 4.70
L	.003 / 0.08	.007 / 0.18
M	.058 / 1.47	.068 / 1.73
N	.119 / 3.02	.135 / 3.43
P	.149 / 3.78	.187 / 4.75

ORDER CODE: ASI10638
CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	I _C = 1.0 mA	45			V
BV_{CER}	I _C = 5.0 mA R _{BE} = 10 Ω	45			V
BV_{EBO}	I _E = 1.0 mA	3.5			V
I_{CBO}	V _{CB} = 28 V			0.5	mA
h_{FE}	V _{CE} = 5.0 V I _C = 500 mA	30		300	---
C_{OB}	V _{CB} = 28 V f = 1.0 MHz			12	pF
P_G	V _{CC} = 21 V I _{CQ} = 200 mA f = 2.7 GHz	4.5			dB
η_C	P _{OUT} = 1.3 W		30		%